

**Silicon PNP Power Transistors**

**2SA1125**

**DESCRIPTION**

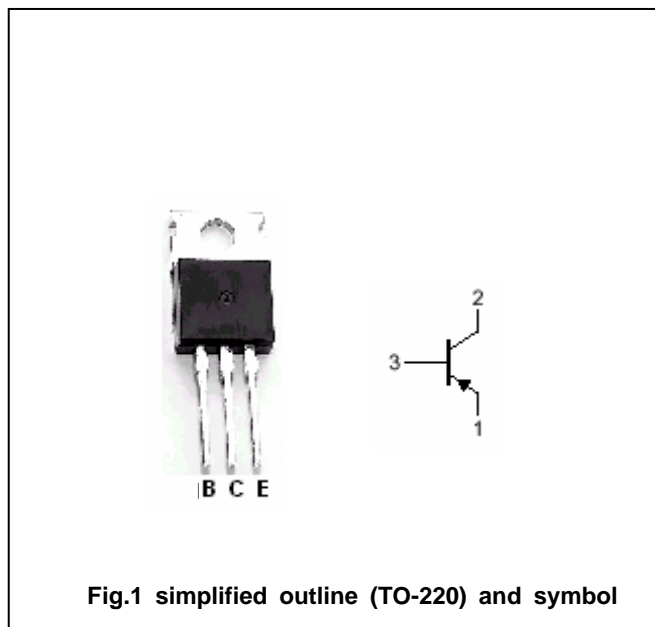
- With TO-220 package
- Complement to type 2SC2633
- High breakdown voltage

**APPLICATIONS**

- For audio frequency high voltage amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-50	mA
I <sub>CM</sub>	Collector current-peak		-100	mA
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	1.5	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-0.1mA, I <sub>B</sub> =0	-150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10 μA, I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =-3mA			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-10mA; V <sub>CE</sub> =-5V	90		450	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz			5	pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-10mA; V <sub>CE</sub> =-10V		200		MHz

◆ h<sub>FE</sub> Classifications

Q	R	S	T
90-155	130-220	185-330	260-450

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PACKAGE OUTLINE

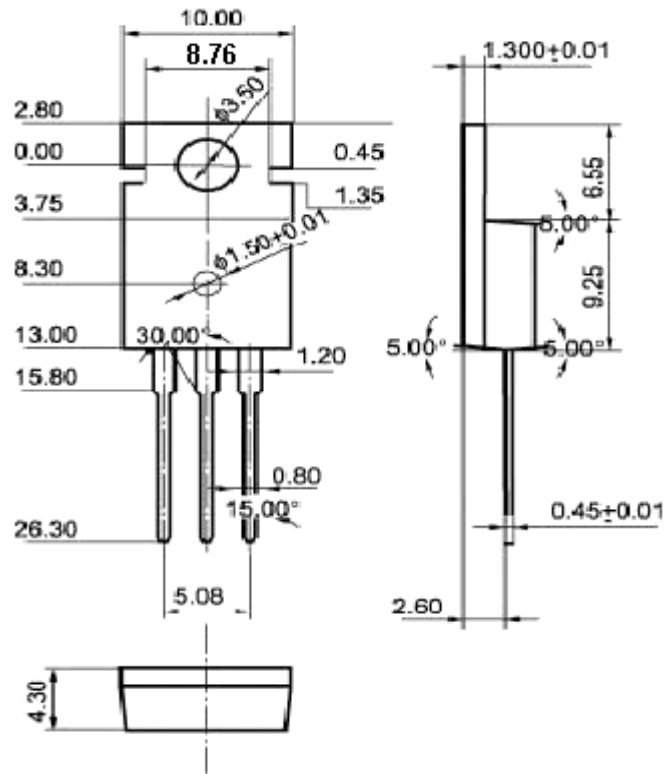


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)